

CORRECTED VERSION

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
22 April 2004 (22.04.2004)

PCT

(10) International Publication Number
WO 2004/034409 A1

(51) International Patent Classification⁷: **H01B 3/30**

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(21) International Application Number:
PCT/US2003/031465

(22) International Filing Date: 3 October 2003 (03.10.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/415,987 4 October 2002 (04.10.2002) US

(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

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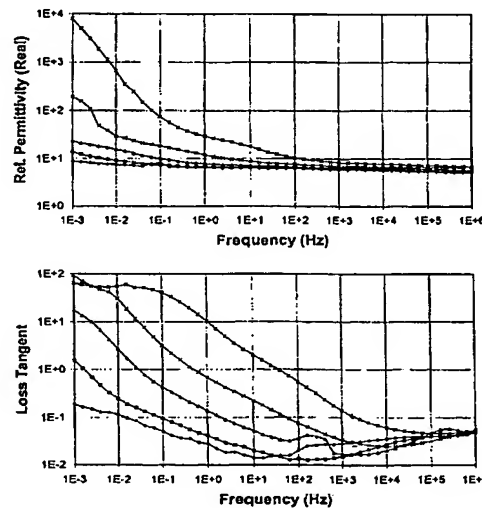
(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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Published:
— with international search report

[Continued on next page]

(54) Title: **NANOMETRIC COMPOSITES AS IMPROVED DIELECTRIC STRUCTURES**



(57) Abstract: A dielectric is provided which possesses high dielectric constant and high dielectric strength, while having the capabilities of a polymer. The dielectric comprises a nanometric composite, which includes a stoichiometric nano- particulate filler embedded in a polymer or resin matrix. Filler particles are reduced in physical size to dimension to the same order as the polymer chain length of the host material and interact cooperatively thereby mitigating the associated Maxwell-Wagner process and reducing interfacial polarization. The internal fields for the new formulation are nearly a factor of 10 lower than for conventional (micro) material. The large changes in the internal field of the composite permit engineering of nanocomposite materials with enhanced electric strength and improved voltage endurance properties.